

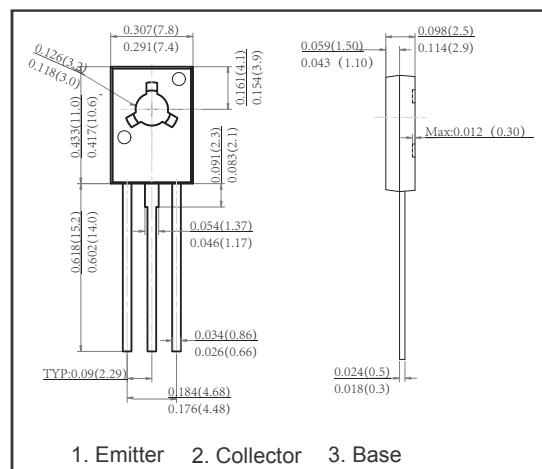
TO-126 Plastic-Encapsulate Transistors

FEATURES

- High Current
- TRANSISTOR (NPN)
- Complement To BD136, BD138 And BD140

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



1. Emitter 2. Collector 3. Base

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage BD135 BD137	V_{CBO}	45	V
		60	
Collector-Emitter Voltage BD135 BD137	V_{CEO}	45	V
		60	
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Collector Power Dissipation	P_C	1.25	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	100	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage BD135 BD137	$V_{(BR)CBO}$	$I_C= 0.1mA, I_E=0$	45 60			V
Collector-emitter sustaining voltage BD135 BD137	$V_{CEO(SUS)}$	$I_C=0.03A, I_B=0$	45 60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1mA, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CE}=30V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=150mA$	40		250	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=5mA$	25			
	$h_{FE(3)}$	$V_{CE}=2V, I_C=500mA$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=2V, I_C=500mA$			1	V

* Pulse test: pulse width ≤350μs, duty cycle≤ 2.0%.

RATINGS AND CHARACTERISTIC CURVES

